

# **IEEE SW Test Workshop**

Semiconductor Wafer Test Workshop

**R. Robertazzi**  
*IBM Research*

**L. Medina, E. Shiling, G. Moore, R. Geiger, J. Liao**  
*IBM Systems and Technology Group*

**J. Williamson**  
*White Eagle Consulting*



## **New Directions In Parametric and Defect Structure Testing**

**June 6 to 9, 2010**

**San Diego, CA USA**



June 6 to 9, 2010

IEEE SW Test Workshop

1

# Acknowledgements

## *V93k pA Project*

- **Verigy Hardware, Software, Project Management**


- Kosuke Miyao.
- Robert Smith.
- Pete Fitzpatrick.
- William Wood.
- Jean Lemaire
- Keith Gross.
- Daniel Lam.
- Don Faller
- David Ting
- Acharyya Dhruva.
- Ken Birdsall
- Karen Herbstman.
- Robert Chisholm.

## *IBM Inline Test Parallel Test Team*

- **IBM Fishkill STG.**
  - Manjul Bhushan.
  - Dave Kiesling.
- **IBM Research**
  - Mark Ketchen



# Outline

- **Motivation: Challenges of monitoring variability moving to 22 nm.**
- **Improving the test process:**
  - Parallel test of parametric macros.
  - Use of array based diagnostics.
  - Improving tester utilization.
-  **Developing the tools required to meet these challenges.**
- **pA Metrology.**
- **Summary.**



# Variability Challenges at 22 nm and Beyond

IBM 300 mm Manufacturing  
Facility, East Fishkill N.Y.

- ➔ Spreads in basic parameters (like  $V_t$ ) are becoming worse. Larger statistics are required.
- Test time for process monitoring can't grow.
  - The manufacturing process must be economically viable. ➔
  - Need to improve test efficiency (*what is tested; how we test*):



# Improving Process Metrology and Test Efficiency

- **Standard Parametric Structures: (Simple macros wired directly to a 1x25 pad cage).**

- Business as usual, but test lots of them.
- Test many in parallel instead of serially.

- **Array Based Parametric Diagnostics.**

- Take advantage of an addressable multiplexer structure to access large numbers of test cells.
- Requires components of both digital and analog test systems.

- **Array Based Digital (Defect)**

- Use on chip electronics and memory like structure to test large numbers of cells quickly.
- Pass / Fail test which uses digital read out circuitry on chip and is fast.



# Traditional In Line Test

Agilent 4073: ~ 6 SMUs



- **Standard Parametric**

- Individual transistors.
- Serps/Combs.
- CV, CBCM.
- PSRO.

- **Array Based Parametric Diagnostics (APDs)**

- Deep statistics on basic process parameters like CA contact resistance,  $V_t$  variability.

- **Array Based Digital**

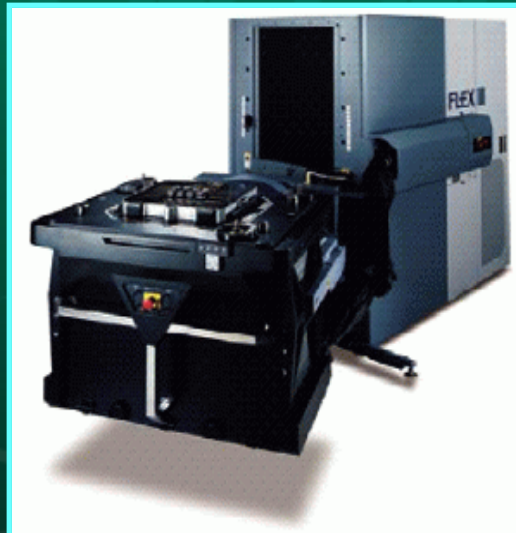
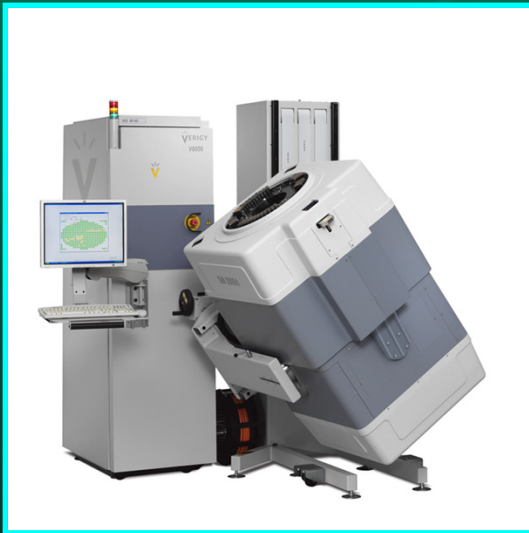
- Defect monitors.
- SRAM.

Verigy 93k: ~1024 Pins





# Lessons From Memory Test: Parallelism



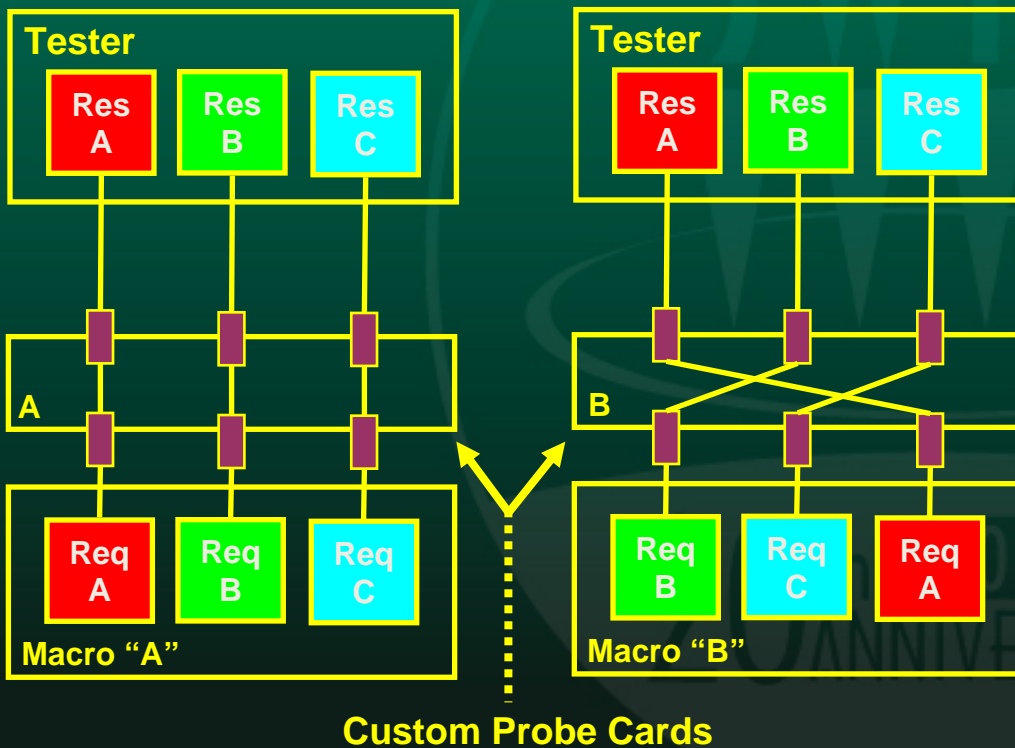
## Multi-DUT Test Systems

 Massive test parallelism improves efficiency, drives down cost.

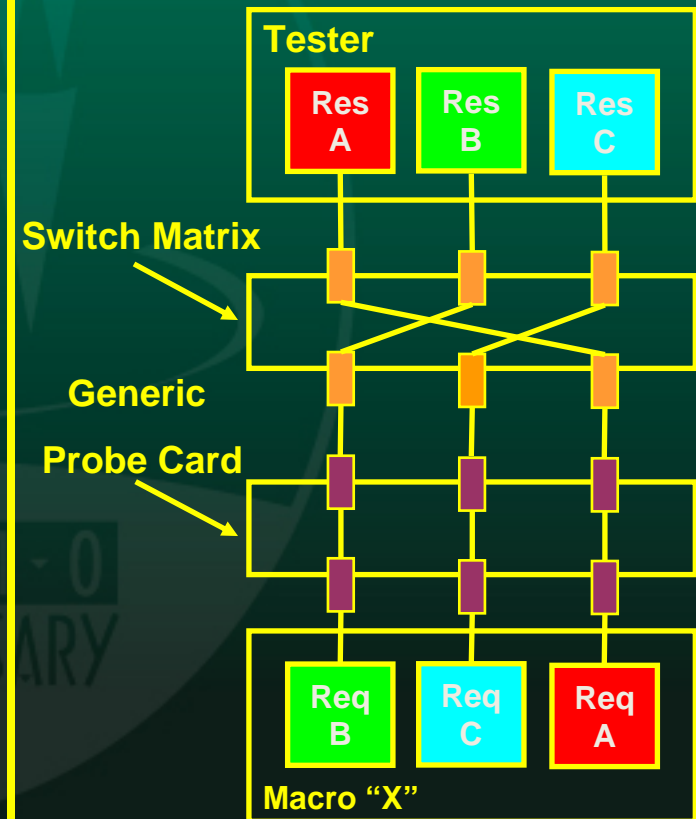


# Lessons From Parametric Test: Software Configurable Interface

## Traditional Digital Test



## Traditional Parametric Test

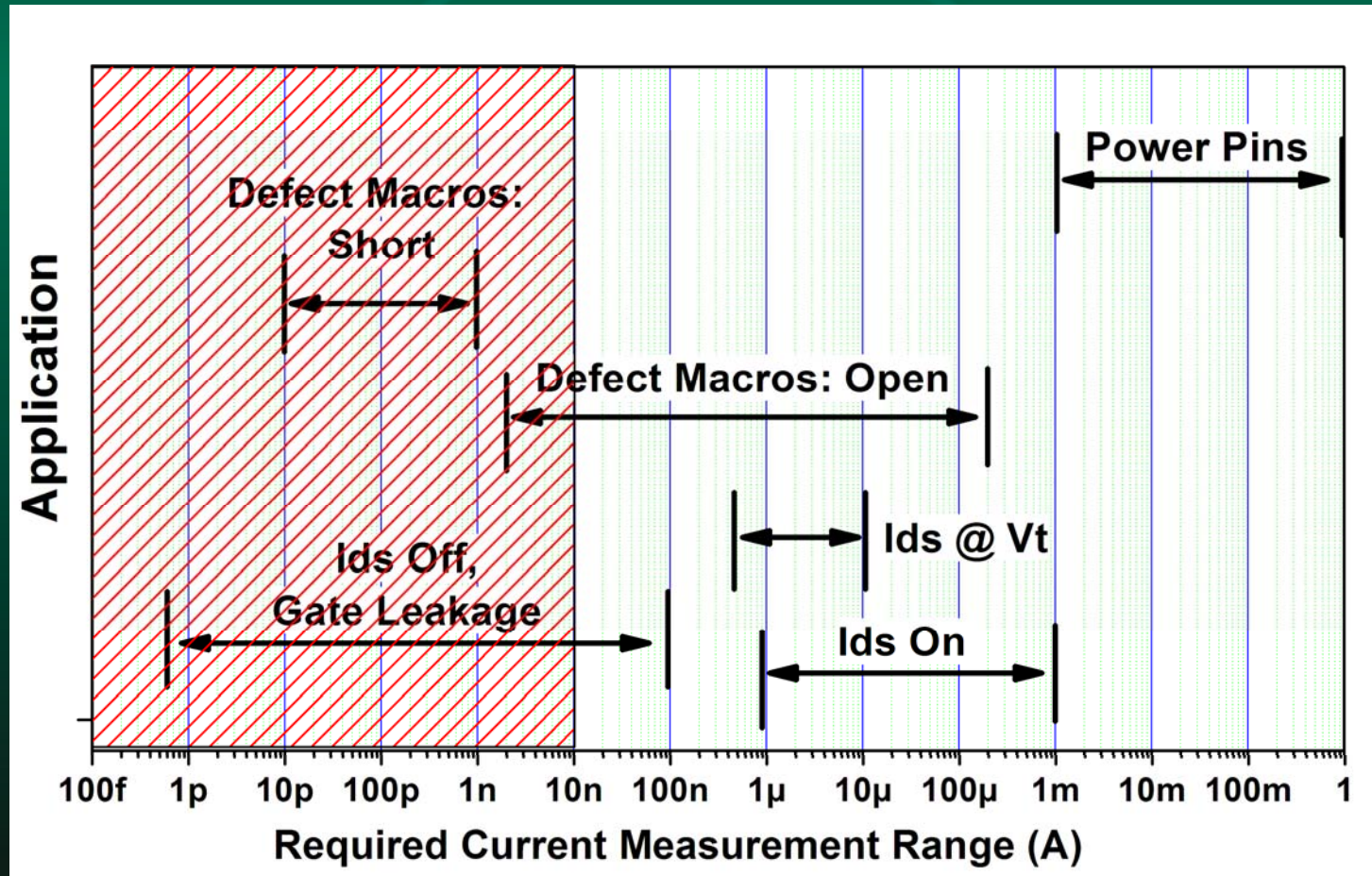


 **Any pin / any function greatly simplifies interfacing to DUT.**





# Current Measurement Range vs. Test Application



- Active and passive device characterization spans many orders of magnitude in current measurement.
- Current levels below **10nA** require specialized SMUs.



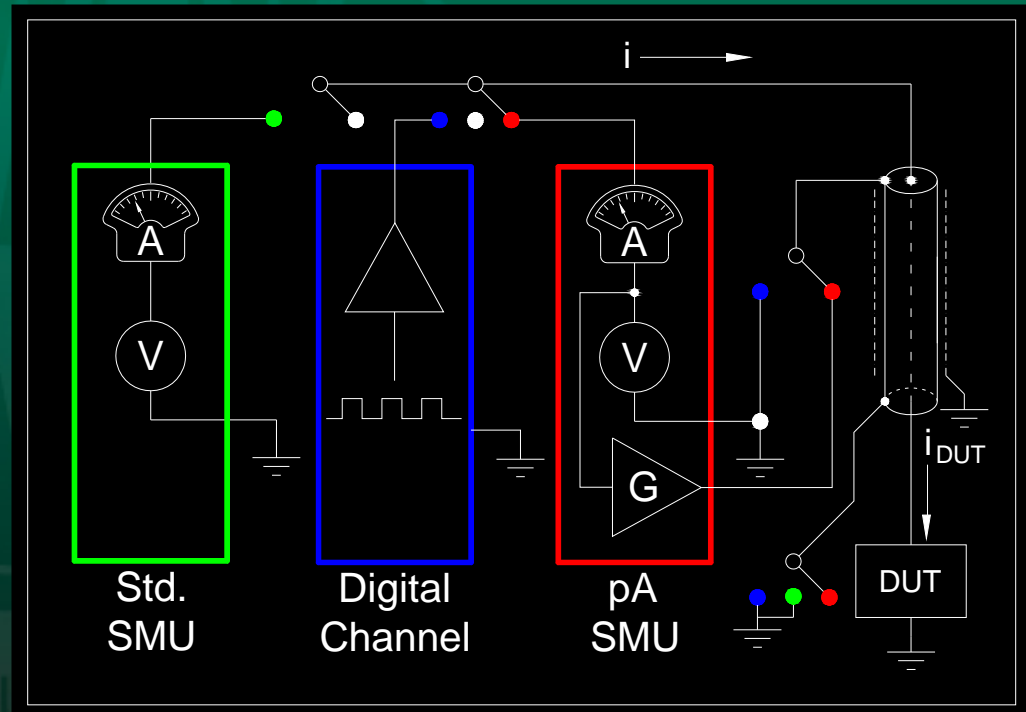
# Hybrid Tester

- Typical digital ATE pin channels possess many of the requirements for parallel test of standard parametric macros, as well as array based and all digital.

- Per pin Source Measurement Unit (SMU).
- Digital I/O capable.

— BUT —

- Low end current measurement range (~10 nA) insufficient for some active and passive parametric tests.
- Enabling full spectrum of active and passive device characterization requires adding an SMU resource with measurement resolution ~1pA
- System **Noise** level must also be low enough for level of metrology required.

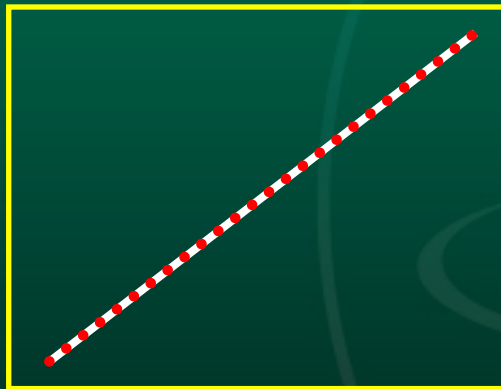


One Channel of Pin Electronics



# Devices: Effects of Noise

Resistor, Linear



V

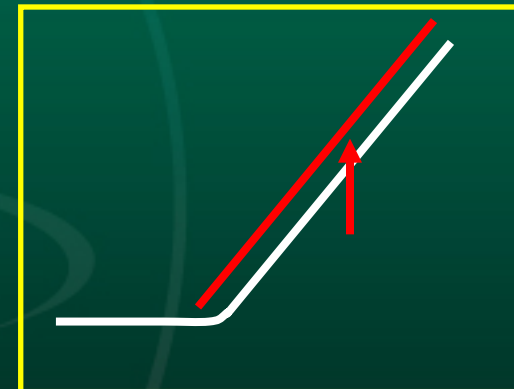
- Linear IV curve.
- **Noise** from SMU will average to zero effect on IV over enough acquisition cycles.

Transistor



Transistor IV will be affected differently at different bias points, depending on whether the IV looks linear, or nonlinear.

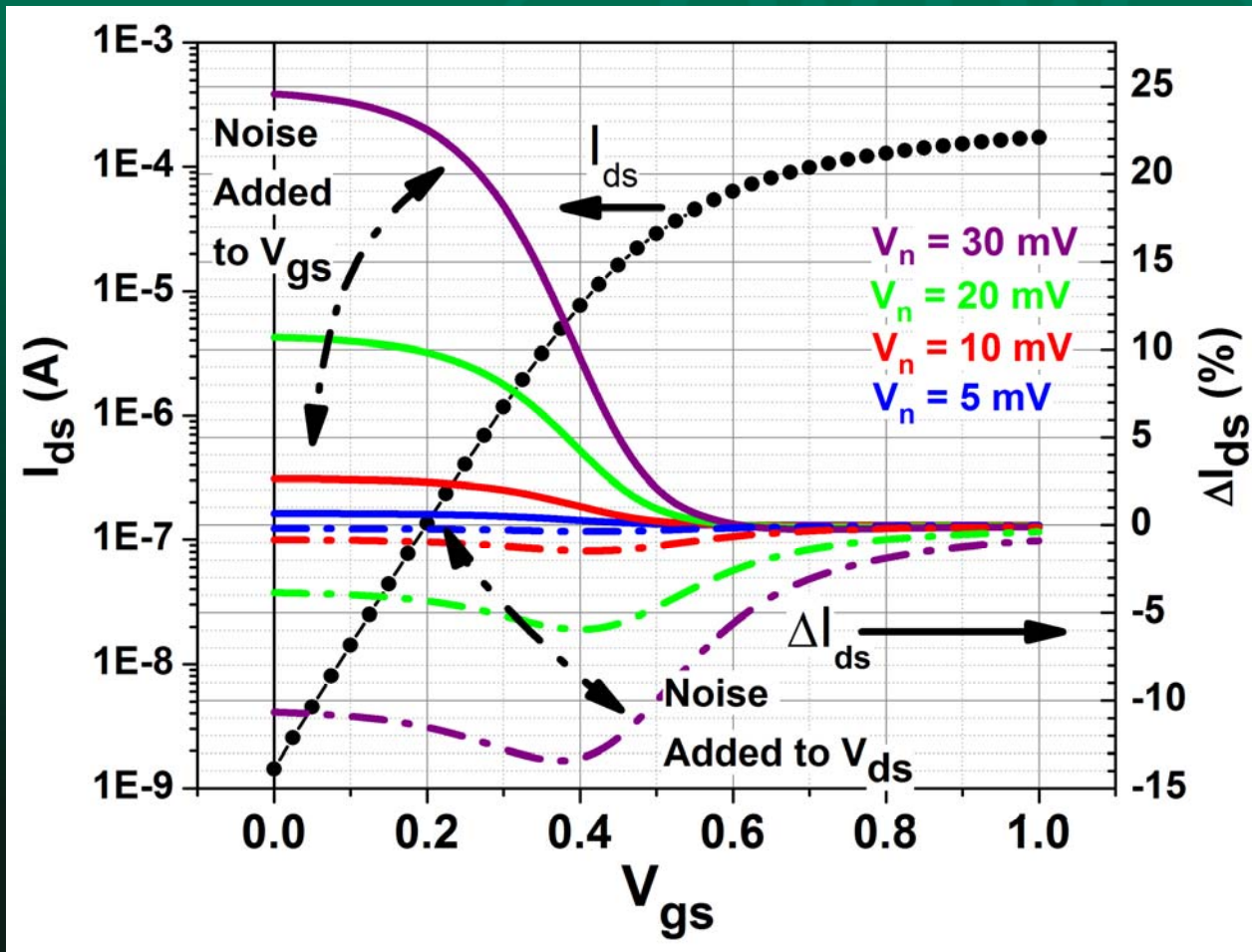
Diode, Nonlinear



V

- IV curve is nonlinear, except in constant current reverse saturation region.
- Noise from SMU will be rectified, shift IV to higher currents.

# NFET IV In Presence of Noise



- Noise on SMUs which establish GND, VGS, or VDS will effect the IV curve.
- Magnitude of the noise term depends strongly on the bias point on the IV.
- Noise effects are minimal where the device looks linear; most pronounced in regions of nonlinear response (sub-threshold).



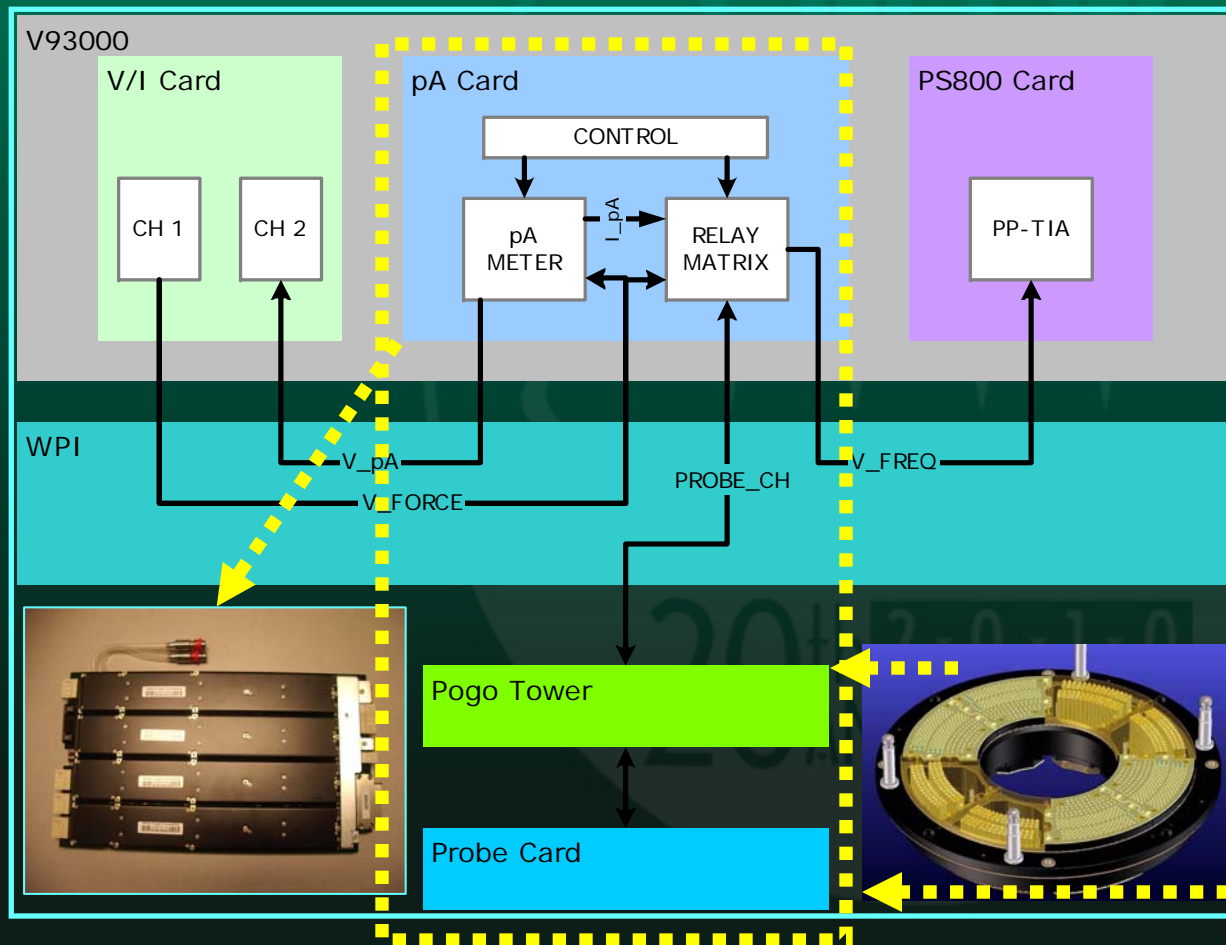
# Implementation

- **Verigy 93k SOC base tester platform.**
  - PS800 digital pin electronics.
  - VI/32 SMU for current range  $I_m > 200$  nA.
- **Newly developed pA SMU for current range  $I_m > 5$  pA.**
- **Low leakage switch matrix enabling steering any tester resource to any of 100 pins.**
- **Low leakage interface enabling current measurements down to pA levels.**
- **Complete integration of all system resources with standard tester software.**



**Verigy 93k**

# 93k DC-Parallel Test Cell



- **pA electronics architecture.**
  - V/I used to set voltage and read I/V converter output.
  - High degree of parallelism in data acquisition, and switch matrix control.
- **Typical data acquisition time 100 ms.**
- **Signal path tightly guarded and air wired inside module.**
- **Pogo tower and cable critical to low noise in a high vibration environment.**

**One Pin of 100**



# Validation



- **In the hardware business, test equipment is our compass.**



June 6 to 9, 2010

IEEE SW Test Workshop

15

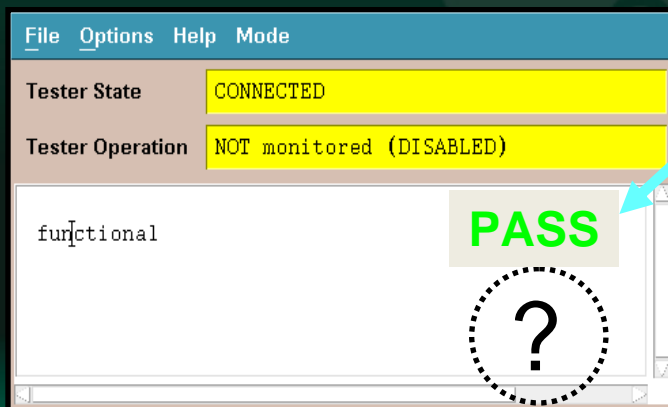


# A Question of Faith



Test

Result



- Large ATE systems provide the means to execute complex tests with great efficiency.
- However, the details of the test process are inherently difficult to observe.

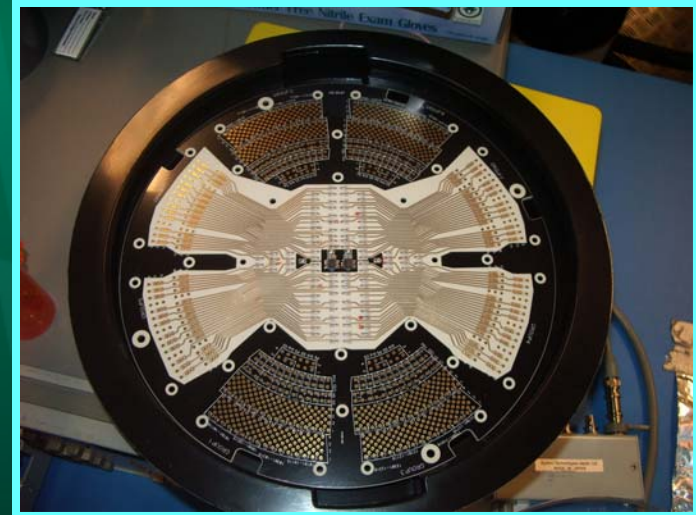


# Validation Methodology

## 1. Validation load board (VLB).

- 40M $\Omega$  and 4G $\Omega$  load boards, 1 load / channel (100 resistors / board).
- Resistors are calibrated at Verigy's Cupertino facility.
- IV curves of the VLB are then compared to measured values on a point by point (typically 18 voltages from -1 to +7.5V).

 No Observability.



## 2. pA Diagnostic instrument.

 Adds observation points. 

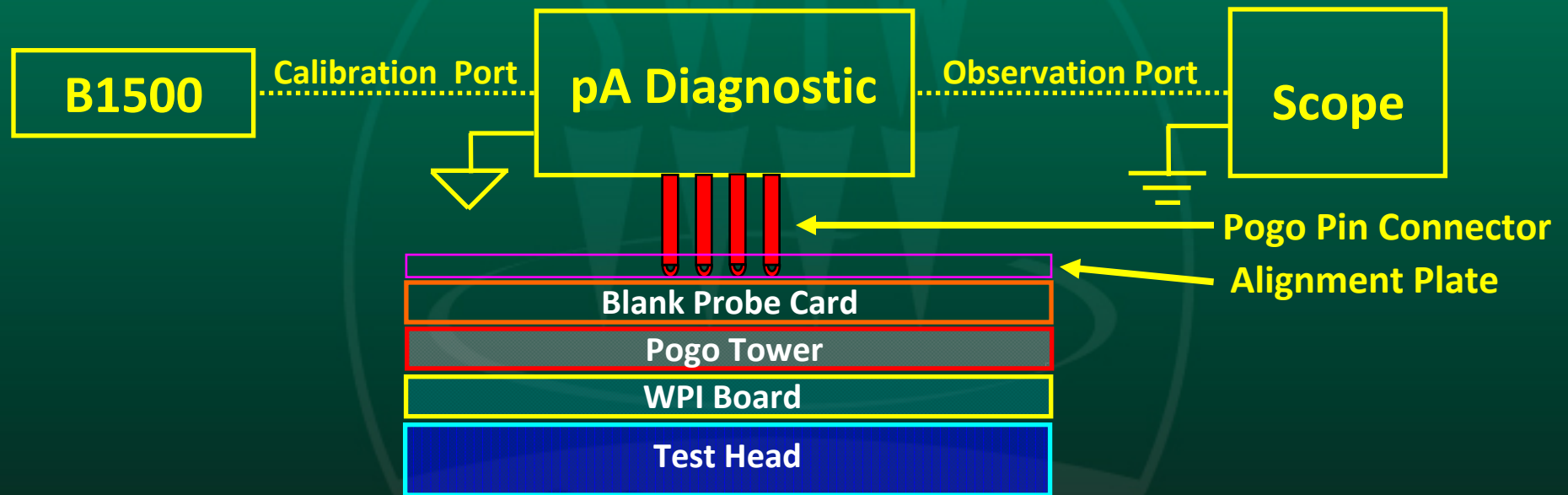
## 3. Verigy NIST traceable calibration instrument.

## 4. Correlation of wafer data from 4073 parametric tester.

- e.g.,  $V_t$  correlation. 



# pA Diagnostic Instrument



- **pA diagnostic**

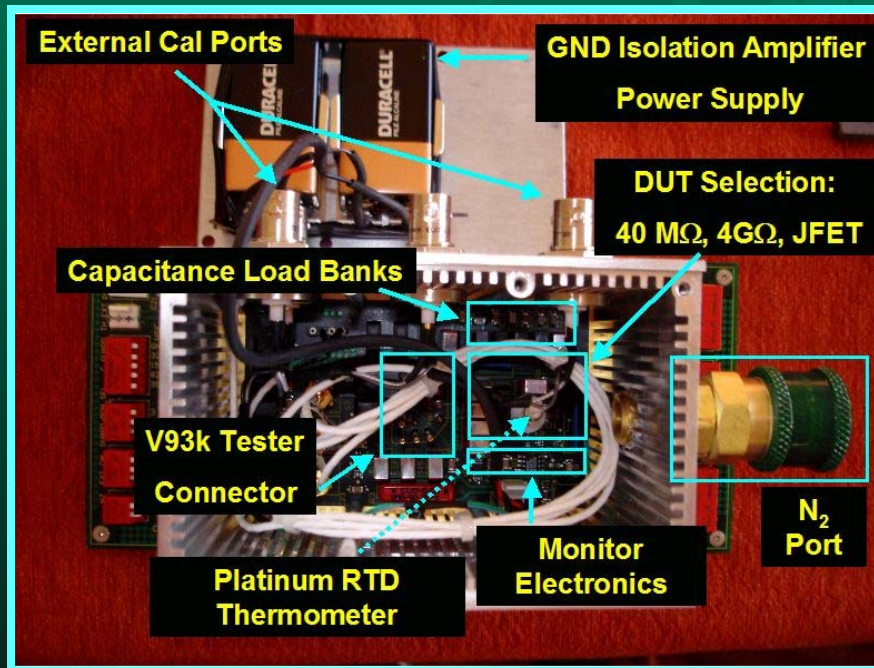
- One selectable precision load used to measure each channel (40 M $\Omega$ , 4 G $\Omega$ , PN junction or N channel JFET).
- Voltage monitors for DUT, and guard (**Observability**).
- Ability to stress measurement and guard channels with large capacitive loads.
- Direct, simple calibration with B1500 or Agilent 4073 provides absolute NIST traceability.





# pA Metrology

## Instrument Details



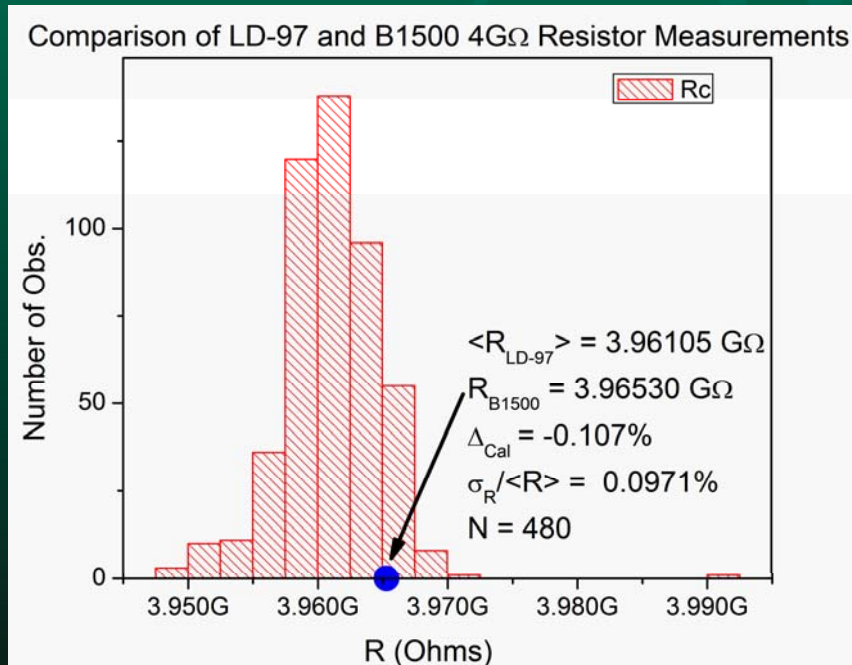
## Parallel Tester Characterization



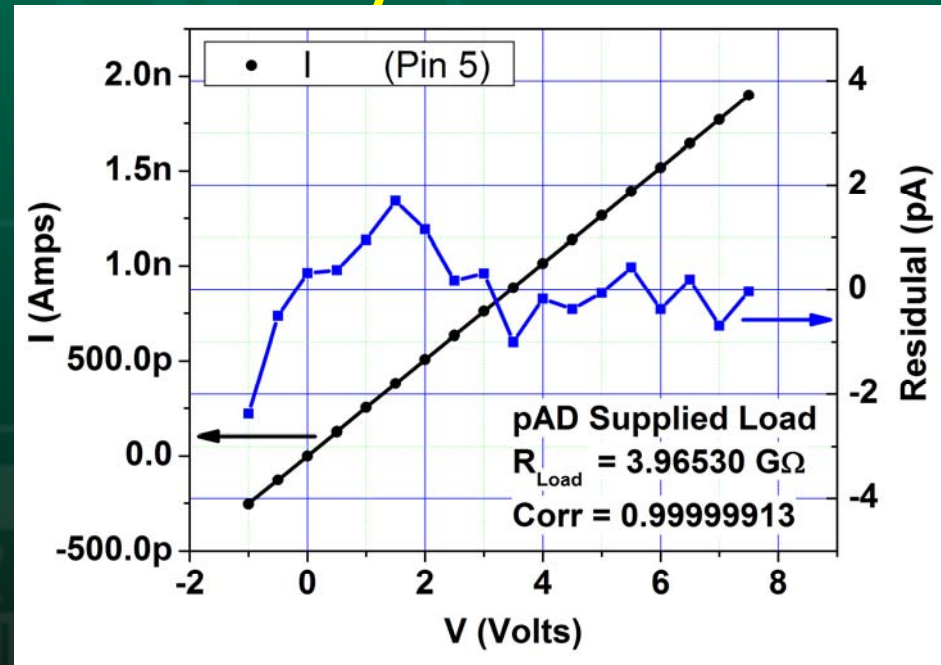
- pA diagnostic enables trouble shooting channels and direct channel to channel comparison with NIST traceable loads.

# Linear Validation

## 4GΩ Resistor Measurement



## Linearity Measurement

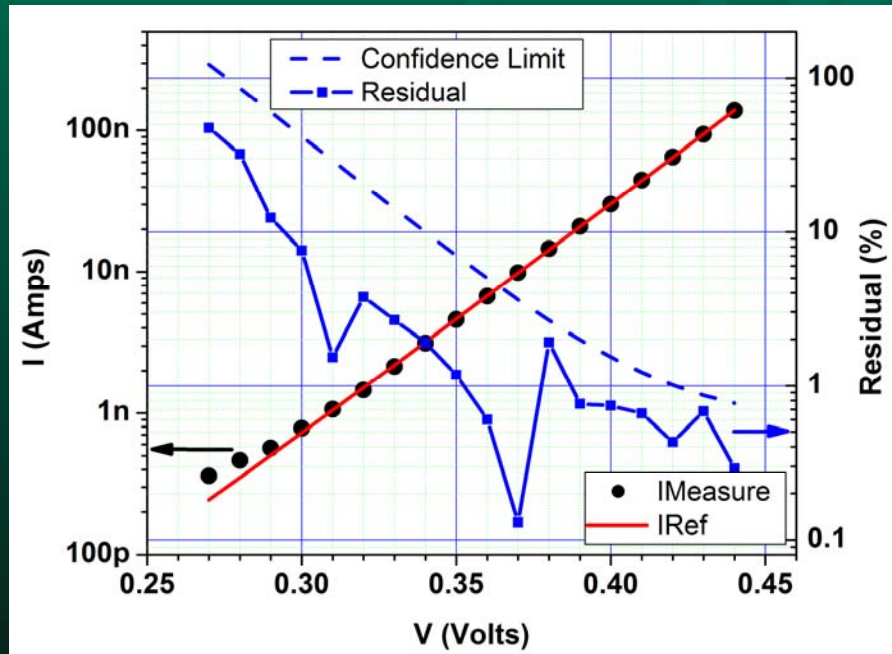


- pA SMU, 2 nA range, 100 ms settling time.
- 48 channel median calibration resistor measurement deviates from B1500 measurement by less than 0.11 %.

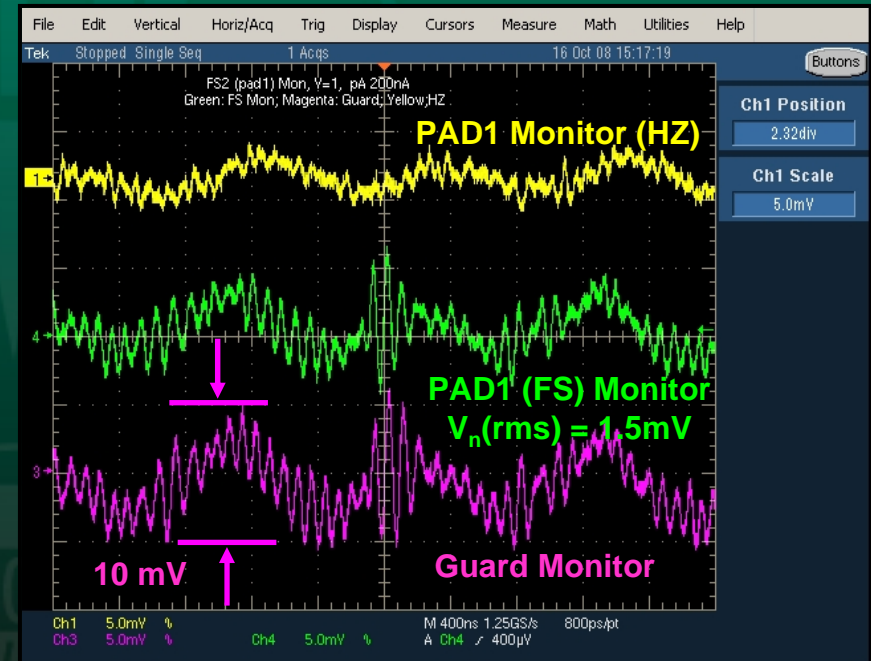


# Nonlinear Validation

## PN Junction IV



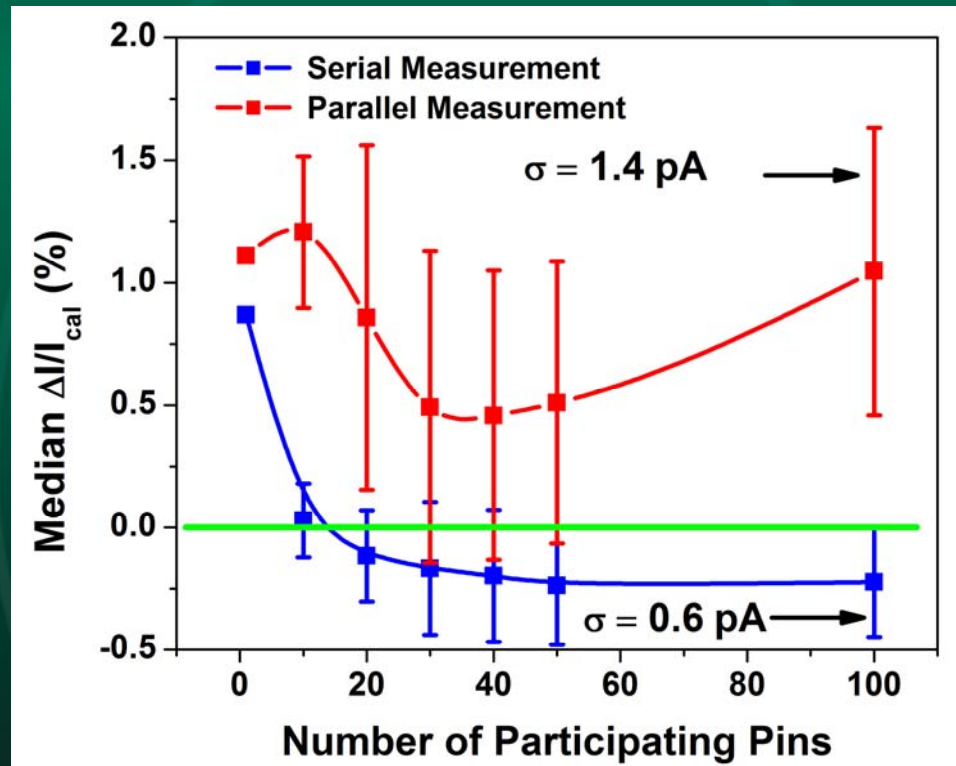
## SMU Noise Characterization



- pA SMU, 200 nA range, 100 ms settling time.
- PN junction IV matches B1500 value within SMU spec. accuracy.
- High impedance monitors allow SMU noise characterization without loading SMU or DUT.



# Serial and Parallel Performance



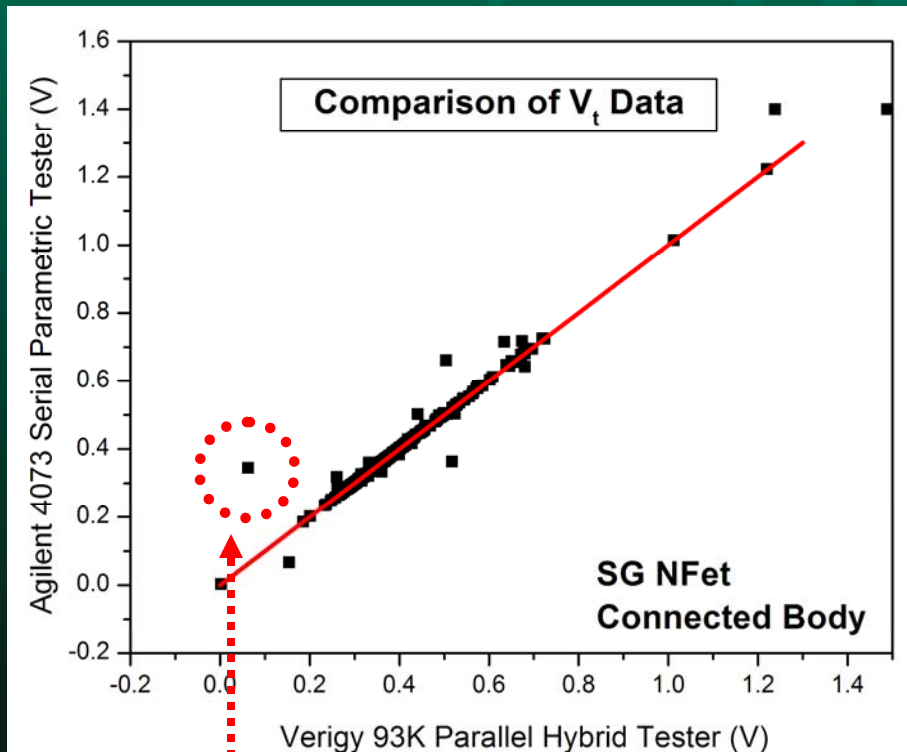
- 1-100 channel VLB measurement, 4GW load, 1V, 250 pA.
- Graph shows median and std. deviation of measurements performed serially and in parallel.
- Full parallel acquisition data demonstrates minimal channel to channel cross coupling (small additional error term  $\sim 1\%$ ,  $<3 \text{ pA}$ ) over measurements made serially.



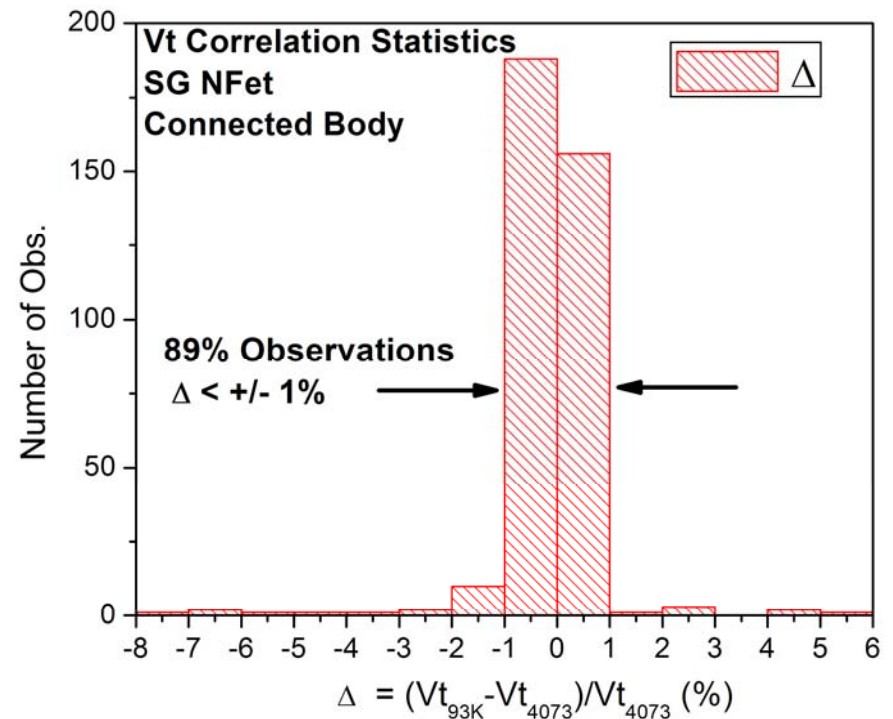


# Wafer Vt Correlation Data

## Correlation



## Statistics



- Wafer correlation work in progress.
- Major focus is elimination of fliers.



# Summary

- **Demonstrated hybrid test system capable of parallel parametric measurements down to pA levels.**
  - 100 channel “any pin any function” for test of standard pad cage parametric macros, digital yield macros, and array based parametric macros.
  - All parametric instrumentation (including pA SMU) integrated with standard test system software.
  - NIST traceable calibration and validation infrastructure.
- **Qualified for manufacturing test of defect structures.**
  - 5X throughput improvement demonstrated.
- **Active device qualification experiments in progress.**

